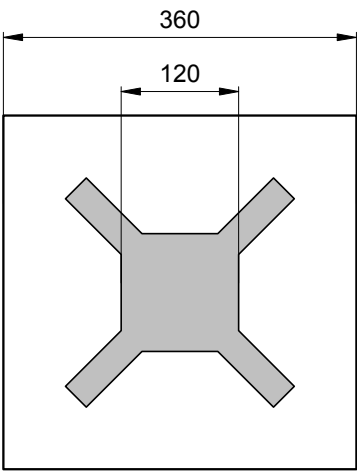


Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	P (anode) up

 <p style="text-align: center;">LED-14</p>	typ. dimensions ( $\mu\text{m}$ )
	<u>typ. thickness</u> 150 ( $\pm 25$ ) $\mu\text{m}$  <u>anode</u> gold alloy, 1.5 $\mu\text{m}$  <u>cathode</u> gold alloy, 0.5 $\mu\text{m}$ dotted, 25% covered

### Optical and Electrical Characteristics

$T_{\text{amb}} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	$V_F$		1.3	1.6	V
Reverse voltage	$I_R = 100 \mu\text{A}$	$V_R$	5			V
Radiant power <sup>1</sup>	$I_F = 20 \text{ mA}$	$\Phi_e$	2.5	3.5		mW
Radiant power <sup>2</sup>	$I_F = 20 \text{ mA}$	$\Phi_e$		7,0		mW
Peak wavelength	$I_F = 20 \text{ mA}$	$\lambda_p$	860	870	890	nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		45		nm
Switching time	$I_F = 20 \text{ mA}$	$t_r, t_f$		12		ns

<sup>1</sup>Measured on bare chip on TO-18 header with *EPIGAP* equipment

<sup>2</sup>Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

### Labeling

Type	Lot N°	$\Phi_e(\text{typ})$ [mW]	$V_F(\text{typ})$ [V]	Quantity
ELC-870-17				

**Packing:** Chips on adhesive film with wire-bond side on top